

PTB 20062

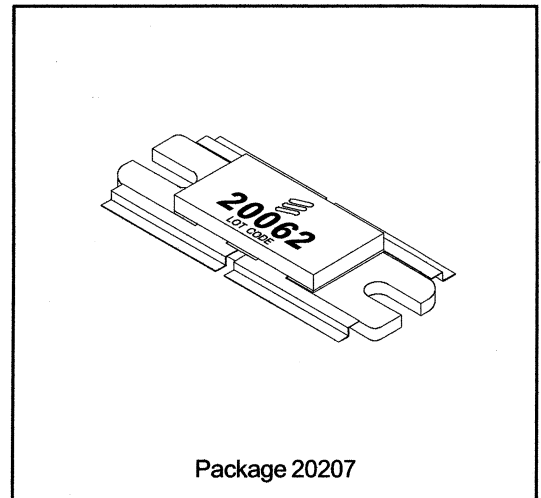
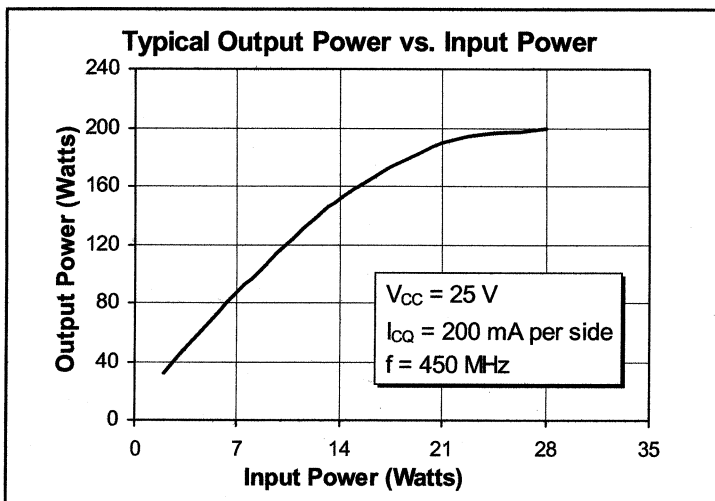
150 Watts, 450–500 MHz

RF Power Transistor

Description

The 20062 is a class AB, NPN, common emitter RF power transistor intended for 25 Vdc operation from 450 to 500 MHz. Rated at 150 watts minimum output power, it may be used for both CW and PEP applications. Ion implantation, nitride surface passivation and gold metallization are used to ensure excellent device reliability. 100% lot traceability is standard.

- 150 Watts, 450–500 MHz
- Class AB Characteristics
- Gold Metallization
- Silicon Nitride Passivated



Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CER}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage (collector open)	V_{EBO}	4.0	Vdc
Collector Current (continuous)	I_C	25	Adc
Total Device Dissipation at $T_{flange} = 25^\circ\text{C}$ Above 25°C derate by	P_D	330 1.89	Watts $\text{W}/^\circ\text{C}$
Storage Temperature	T_{stg}	150	$^\circ\text{C}$
Thermal Resistance ($T_{flange} = 70^\circ\text{C}$)	$R_{\theta JC}$	0.53	$^\circ\text{C}/\text{W}$

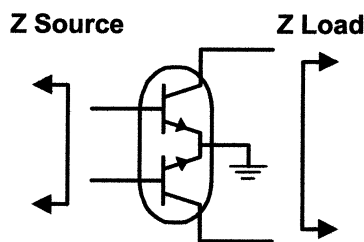
Electrical Characteristics (100% Tested)

Characteristic	Conditions	Symbol	Min	Typ	Max	Units
Breakdown Voltage C to E	$I_B = 0\text{ A}, I_C = 100\text{ mA}$	$V_{(BR)CEO}$	25	30	—	Volts
Breakdown Voltage C to E	$V_{BE} = 0\text{ V}, I_C = 100\text{ mA}$	$V_{(BR)CES}$	55	70	—	Volts
Breakdown Voltage E to B	$I_C = 0\text{ A}, I_E = 5\text{ mA}$	$V_{(BR)EBO}$	3.5	5.0	—	Volts
DC Current Gain	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	h_{FE}	20	50	100	—

RF Specifications (100% Tested)

Characteristic	Symbol	Min	Typ	Max	Units
Gain ($V_{CC} = 25\text{ Vdc}, P_{out} = 150\text{ W}, I_{CQ} = 200\text{ mA per side}, f = 450\text{--}500\text{ MHz}$)	G_{pe}	10.0	11.5	—	dB
Collector Efficiency ($V_{CC} = 25\text{ Vdc}, P_{out} = 150\text{ W}, I_{CQ} = 200\text{ mA per side}, f = 450\text{--}500\text{ MHz}$)	η_C	55	60	—	%
Load Mismatch Tolerance ($V_{CC} = 25\text{ Vdc}, P_{out} = 150\text{ W}, I_{CQ} = 200\text{ mA per side}, f = 450\text{--}500\text{ MHz}$ —all phase angles at frequency of test)	Ψ	—	—	5:1	—

Impedance Data



Frequency MHz	Z Source		Z Load	
	R	jX	R	jX
450	0.3	-0.8	1.6	0.2
500	0.4	-0.9	1.4	0.0

